

ATES PATENT AND TRADEMARK OFFICE

Applicant: Koichiro Tanaka

Art Unit : 2822

Serial No.: 09/842,797

Examiner: Maria F. Guerrero

Filed

: April 27, 2001

Title

: METHOD OF FABRICATING SEMICONDUCTOR DEVICE

MAIL STOP AMENDMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Applicants request consideration of the references listed on the attached PTO-1449 form. Under 37 C.F.R. § 1.98 (a)(2)(ii), only copies of foreign patent documents and/or non-patent literature are enclosed. Copies of any U.S. patents or U.S. patent application publications can be provided upon request.

This statement is being filed after a first Office action on the merits, but before receipt of a final Office action or a Notice of Allowance. A check for \$180 in payment of the late submission fee of §1.17(p) is enclosed. Please apply any other charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

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U.S. Department of Commerce Patent and Fademark Office Attorney's Docket No. 12732-034001

Application No. 09/842,797

Information Disclosure Statement by Applicant (Use several sheets if necessary) Applicant Koichiro Tanaka

April 27, 2001

Filing Date

Group Art Unit 2822

(37 CFR §1.98(b))

U.S. Patent Documents Filing Date Document Publication Desig. Examiner Patentee Class Subclass If Appropriate Number Date Initial ID 01/25/1982 AA 4,439,245 03/27/1984 WU AB ACAD ΑE AF AG AH ΑI ΑJ ΑK

Foreign Patent Documents or Published Foreign Patent Applications									
Examiner	Desig.	Document	Publication	Country or			Translation		
Initial	ID	Number	Date	Patent Office	Class	Subclass	Yes	No	
	AL								
	AM								
	AN								
	AO								
	AP								

(Other Documents (include Author, Title, Date, and Place of Publication)						
Examiner Initial	Desig. ID	Document					
	AQ	Hayashi et al., "FABRICATION OF LOW-TEMPERATURE BOTTOM-GATE POLY-SI TFTS ON LARGE-AREA SUBSTRATE BY LINEAR-BEAM EXCIMER LASER CRYSTALLIZATION AND ION DOPING METHOD," IEDM '95; Technical Digest of International Electron Devices Meeting, 33.3.1 – 33.3.4, pp. 829-832, December 10-13, 1995.					
	AR	·					
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	AT						

Examiner Signature	Date Considered				
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.					